
3-Phase BLDC Motor Driver IC

ECN30114 Product Specification

Rev. 1

1. Product Description

1.1 Features

- (1) Maximum Ratings: 250VDC/1.4A, suitable for the system from 100VAC to 120VAC
- (2) Drives a motor using high voltage PWM (Pulse Width Modulation) control and increases efficiency
- (3) Variable speed control by an analog speed command signal (VSP signal)
- (4) Six IGBTs, six FWDs (Free-Wheeling Diodes), drivers for IGBTs, protection circuits, etc. integrated into a single chip, resulting in space reduction
- (5) Drives a motor using a high voltage DC power supply and a low voltage DC power supply (15V)

1.2 Functions

- (1) Hall elements applicable (Hall amplifiers are embedded)
- (2) Power on/off sequence-free
- (3) Charge pump circuit (built-in high voltage diodes for charge pump)
- (4) FG (Frequency Generator) signal outputs for motor rotational speed monitor
- (5) All IGBT shutoff function
- (6) Current limit function (detects at 0.5V)
- (7) Vcc low-voltage detection function
- (8) Over temperature protection function
- (9) PWM circuit (enable 20kHz PWM operation)
- (10) Three-phase distributor circuit

1.3 Block Diagram

The ECN30114 is shown inside the bold line.

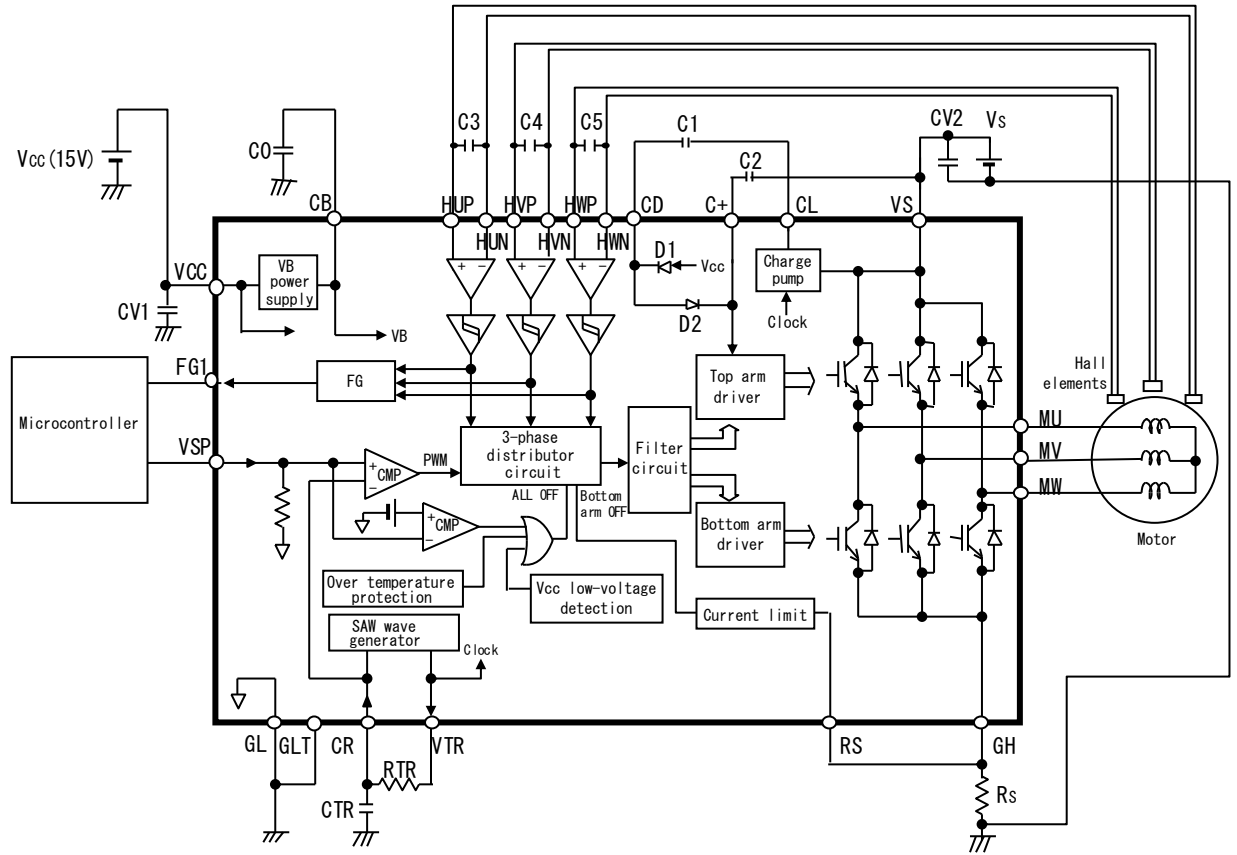
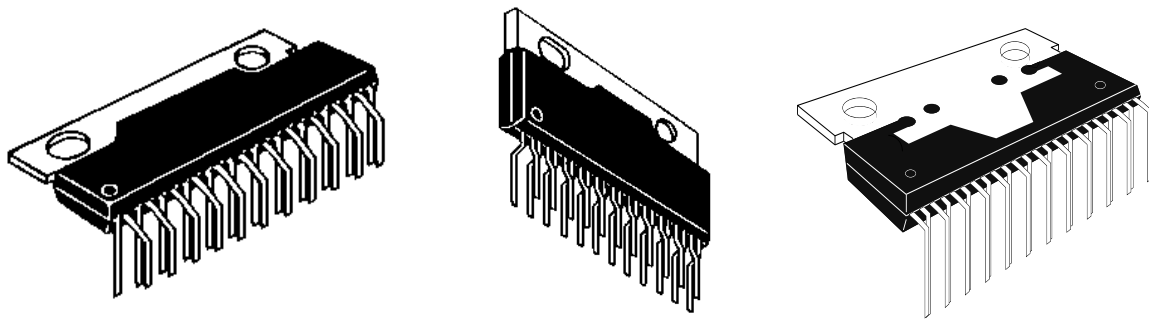


FIGURE 1.3.1 Block Diagram

1.4 Packages



ECN30114SP

ECN30114SPV

ECN30114SPR

FIGURE 1.4.1 Packages of ECN30114

2. Specification

2.1 Maximum Ratings

TABLE 2.1.1 Maximum Ratings

Condition: Ta=25°C

| No. | Item | Symbol | Pin | Rating | Unit | Condition |
|-----|---------------------------------|--------|---|----------------|------|-----------|
| 1 | Output device withstand voltage | VSM | VS, CL, CD, MU, MV, MW | 250 | V | |
| 2 | Vcc power supply voltage | VCC | VCC | 18 | V | |
| 3 | Voltage between C+ and VS | VCPM | C+, VS | 18 | V | |
| 4 | Input voltage | VIN | VSP, RS, HUP, HUN, HVP, HVN, HWP, HWN | -0.5 to VB+0.5 | V | |
| 5 | Output current | Pulse | MU, MV, MW | 1.4 | A | Note 1 |
| 6 | | DC | | 1.0 | | |
| 7 | VB supply output current | IBMAX | CB | 50 | mA | |
| 8 | Junction operating temperature | Tjop | — | -40 to +135 | °C | Note 2 |
| 9 | Storage temperature | Tstg | — | -40 to +150 | °C | |

Note 1: Output IGBTs can handle this peak current.

Note 2: Thermal resistance

Between junction and case: Rjc = 4°C/W (Reference value)

Note 3: This IC withstands 305V for 1 minute assuming a temporary incorrect connection of the Vs power supply.

2.2 Electrical Characteristics

TABLE 2.2.1 Electrical Characteristics (1/2) Suffix (T: Top arm, B: Bottom arm) Condition: Ta=25°C

| No. | Item | | Symbol | Pin | Min. | Typ. | Max. | Unit | Condition | |
|-----|---|------------------------------|---------|---|------|------|------|-------|---|--------------------------------|
| 1 | Standby current | | ISH | VS | — | 0.1 | 0.4 | mA | VSP=0V, VS=141V, VCC=15V | |
| 2 | | | ICC | VCC | — | 4 | 10 | mA | VSP=0V, VCC=15V, IB=0A | |
| 3 | IGBT collector-emitter saturation voltage | | VONT | MU, | — | 2.0 | 3.0 | V | I=0.7A, VCC=15V | |
| 4 | | | VONB | MV, MW | — | 2.0 | 3.0 | V | | |
| 5 | Free-wheeling diode forward voltage | | VFDT | | — | 1.7 | 2.5 | V | I=0.7A | |
| 6 | | | VFDB | | — | 1.7 | 2.5 | V | | |
| 7 | VTR output resistance | | RVTR | VTR | — | 200 | 400 | Ω | IVTR=±1mA, VCC=15V | |
| 8 | SAW wave | High/Low level | VSAWH | CR | 4.9 | 5.4 | 5.9 | V | VCC=15V | |
| 9 | | | VSAWL | | 1.7 | 2.1 | 2.4 | V | | |
| 10 | | Amplitude | VSAWW | | 2.8 | 3.3 | 3.8 | V | | VCC=15V Note 1 |
| 11 | Current limit | Reference voltage | Vref1 | RS | 0.45 | 0.50 | 0.55 | V | VCC=15V | |
| 12 | | Delay time | Tref1 | | 1.7 | 2.5 | 5.0 | μs | | |
| 13 | RS input current | | IILRS | RS | -100 | — | — | μA | VCC=15V, RS=0V Note 5 | |
| 14 | Hall signal input | Minimum differential voltage | VHOS | HUP, HUN, HVP, HVN, HWP, HWN | 60 | — | — | mVp-p | VCC=15V Note 2 | |
| 15 | | Current | IH | | — | — | 2 | μA | | |
| 16 | | Common mode voltage range | VHCM | | 3 | — | 6 | V | | |
| 17 | | Hysteresis | VHHYS | | 20 | 40 | 60 | mV | | |
| 18 | | Voltage L→H | VHLH | | -5 | 20 | 45 | mV | | |
| 19 | | Voltage H→L | VHHL | | -45 | -20 | 5 | mV | | |
| 20 | VSP input | Current | IVSPH | VSP | 5 | — | 100 | μA | VSP=5.0V, VCC=15V Pull-down resistor Note 3 | |
| 21 | | Offset voltage | SPCOMOF | | -40 | 60 | 160 | mV | | VCC=15V Voltage from CR pin |
| 22 | | All off operating voltage | Voff | | 0.85 | 1.23 | 1.60 | V | | VCC=15V |
| 23 | VB supply output | Voltage | VB | CB | 6.8 | 7.5 | 8.2 | V | VCC=15V, IB=0A | |
| 24 | | Current | IB | | — | — | 45 | mA | | VCC=15V |
| 25 | FG1 output resistance | | RFGP | FG1 | — | 0.9 | 3.0 | kΩ | IFG=1mA, VCC=15V Note 4 | |
| 26 | | | RFGN | | — | 0.4 | 1.5 | kΩ | | IFG= -1mA, VCC=15V Note 4 |
| 27 | Vcc low-voltage detection | Operating voltage | LVSDON | VCC, MU,MV, MW | 11.0 | 12.0 | 12.9 | V | | |
| 28 | | Recovery voltage | LVSDOFF | | 11.1 | 12.5 | 13.0 | V | | |
| 29 | Minimum pulse width (bottom arms) | | TMINB | MU,MV, MW | 0.8 | — | — | μs | VCC=15V Note 6 | |
| 30 | Charge pump diode forward voltage | | VFDCP | VCC,CD, C+ | — | 0.8 | 1.4 | V | I=1mA | |

TABLE 2.2.1 Electrical Characteristics (2/2) Suffix (T: Top arm, B: Bottom arm) Condition: Ta=25°C

| No. | Item | | Symbol | Pin | Min. | Typ. | Max. | Unit | Condition |
|-----|-----------------------------|-----------------------|--------|------------|------|------|------|------|-----------|
| 31 | Over temperature protection | Operating temperature | TSDON | MU, MV, MW | 140 | 170 | 195 | °C | VCC=15V |
| 32 | | Recovery temperature | TSDOFF | | 115 | 145 | 170 | °C | |

Note 1: The amplitude of SAW wave (i.e., VSAWW) is determined by the following equation.

$$VSAWW = VSAWH - VSAWL (V)$$

Note 2: The equivalent circuit is shown in FIGURE 2.2.1.

Note 3: Internal pull-down resistor is typically 320kΩ. The equivalent circuit is shown in FIGURE 2.2.2.

Note 4: The equivalent circuit is shown in FIGURE 2.2.3.

Note 5: Internal pull-up resistor is typically 200kΩ. The equivalent circuit is shown in FIGURE 2.2.4.

Note 6: The minimum pulse width to pass the filter circuit.

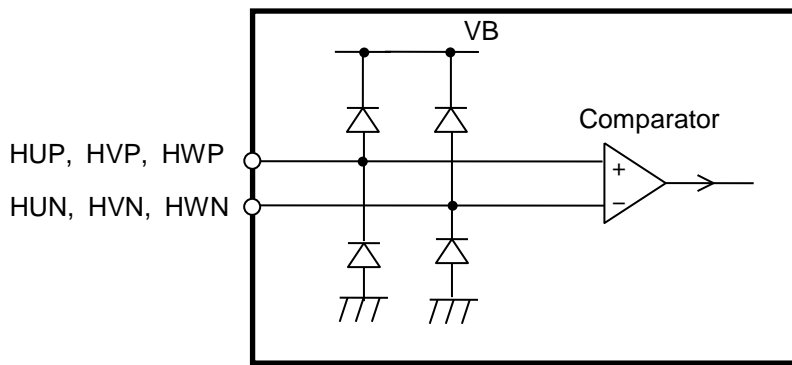


FIGURE 2.2.1 Equivalent Circuit around Hall Signal Pins

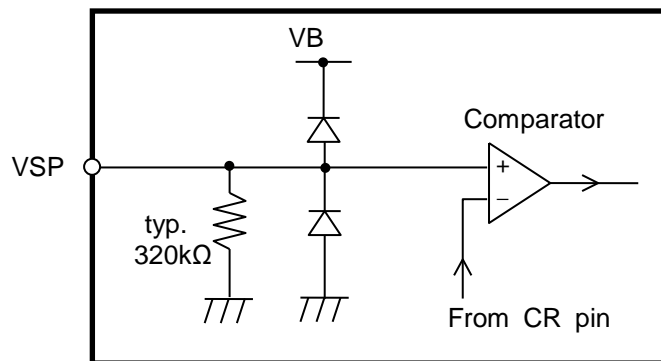


FIGURE 2.2.2 Equivalent Circuit around VSP Pin

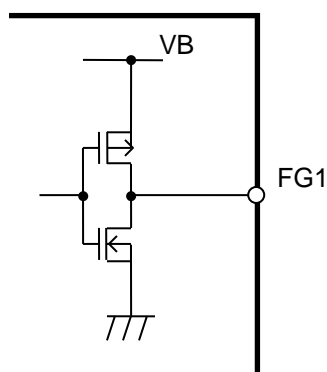


FIGURE 2.2.3 Equivalent Circuit around FG1 Pin

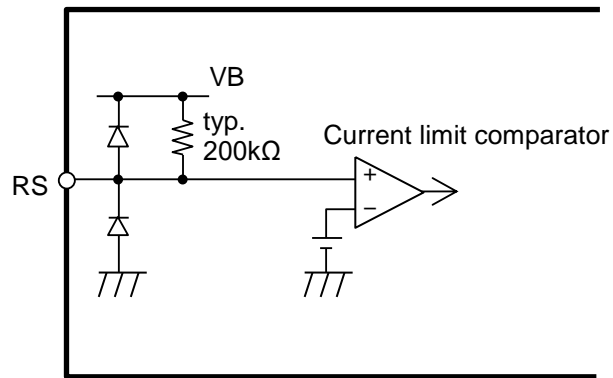


FIGURE 2.2.4 Equivalent Circuit around RS Pin

2.3 Operating Condition

TABLE 2.3.1 Operating Condition

| No. | Item | Symbol | Pin | Min. | Typ. | Max. | Unit |
|-----|----------------|--------|-----|------|------|------|------|
| 1 | Supply voltage | VSop | VS | 15 | 141 | 210 | V |
| 2 | | VCCop | VCC | 13.5 | 15.0 | 16.5 | V |

2.4 Functions and Operations

2.4.1 Truth Table

TABLE 2.4.1.1 Truth Table

| Mode | Hall signal input | | | Phase-U | | Phase-V | | Phase-W | | FG1 output |
|------|-------------------|----|----|---------|------------|---------|------------|---------|------------|------------|
| | HU | HV | HW | Top arm | Bottom arm | Top arm | Bottom arm | Top arm | Bottom arm | |
| (1) | H | L | H | OFF | ON | ON | OFF | OFF | OFF | H |
| (2) | H | L | L | OFF | ON | OFF | OFF | ON | OFF | L |
| (3) | H | H | L | OFF | OFF | OFF | ON | ON | OFF | H |
| (4) | L | H | L | ON | OFF | OFF | ON | OFF | OFF | L |
| (5) | L | H | H | ON | OFF | OFF | OFF | OFF | ON | H |
| (6) | L | L | H | OFF | OFF | ON | OFF | OFF | ON | L |
| — | L | L | L | OFF | OFF | OFF | OFF | OFF | OFF | L |
| — | H | H | H | OFF | OFF | OFF | OFF | OFF | OFF | H |

Note: Inputs H: Input voltage between H*P and H*N > VHLH
 Inputs L: Input voltage between H*P and H*N < VHHL

2.4.2 Timing Chart

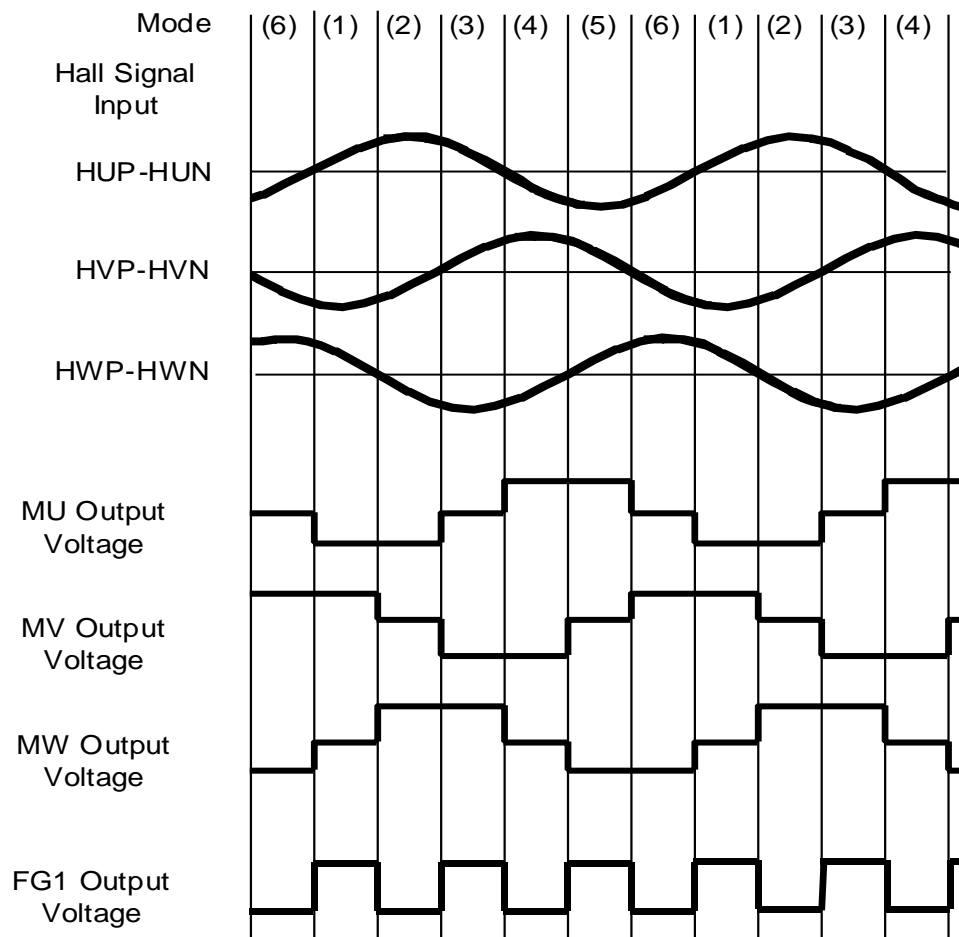


FIGURE 2.4.2.1 Timing Chart

2.4.3 PWM Operation

The PWM signal is generated by comparing the input voltage at the VSP pin with an internal SAW wave voltage (available at the CR pin). The relation between VSP input voltage and PWM duty is shown in FIGURE 2.4.3.1. The PWM duty represents the duty of IGBT gate drive signals. The voltages at output pins (MU, MV, MW) may be different from the figure depending on conditions. The PWM is operated by bottom arms.

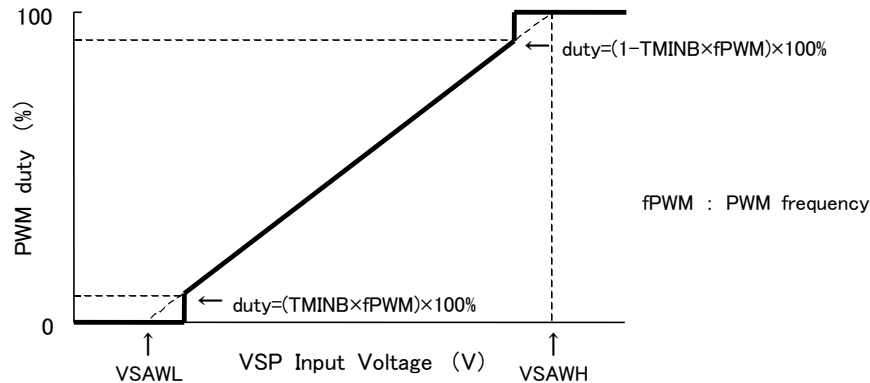


FIGURE 2.4.3.1 Relation between VSP Input Voltage and PWM Duty

2.4.4 Current Limit

This IC detects current using an external shunt resistor Rs. When the voltage at the shunt resistor Rs exceeds the current limit reference voltage (Vref1, typ. 0.5V), all bottom arm IGBTs are turned off. This off state is automatically reset once per internal CLOCK period (available at VTR pin).

2.4.5 Vcc Low-voltage Detection

When Vcc voltage drops below the operating voltage of the Vcc low-voltage detection (LVSDON), all IGBTs (top and bottom arms) are turned off. When Vcc voltage goes up above the recovery voltage of the Vcc low-voltage detection (LVSDOFF), the IC returns to the state in which the IGBTs operate depending on input signals.

When the IGBTs of the top and bottom arms are all turned off by operation of this function or other function during motor driving, the power supply voltage may rise as a result of a regenerative current flow. The power supply voltage must not exceed the maximum rating (250V).

2.4.6 All IGBT Shutoff Function

When the input voltage at the VSP pin drops below VSAWL (typ. 2.1V), the IC stops the motor drive. When the input voltage at the VSP pin drops further from VSAWL and becomes below Voff (typ. 1.23V), the IGBTs (top and bottom arms) are all shut off to reduce current consumption within the IC.

The state of the output IGBTs with regard to the VSP input voltage is shown in Table 2.4.6.1.

TABLE 2.4.6.1 IGBT Operation to VSP Input Voltage

| VSP input voltage | Motor drive state | Top arm IGBTs | Bottom arm IGBTs |
|-------------------------|-------------------|------------------------|------------------------|
| $0V \leq VSP < Voff$ | Stop | All OFF | All OFF |
| $Voff \leq VSP < VSAWL$ | | Based on TABLE 2.4.1.1 | All OFF |
| $VSAWL \leq VSP$ | Drive | Based on TABLE 2.4.1.1 | Based on TABLE 2.4.1.1 |

2.4.7 Over Temperature Protection

When IC temperature exceeds the operating temperature of over temperature protection (TSDON), all IGBTs (top and bottom arms) are turned off. When IC temperature goes below the recovery temperature of over temperature protection (TSDOFF), the IC returns to the state in which the IGBTs operate depending on input signals.

2.4.8 Power On/Off Sequence-free

IGBT current saturation does not occur regardless of power on/off sequence of the Vcc power supply, Vs power supply and VSP input voltage.

3. Standard Applications

3.1 External Components

TABLE 3.1.1 External Components

| Component | Standard value | Usage | Remark |
|------------|-----------------|--|--------|
| C0 | 1.0μF±10%, 25V | Smooths the internal power supply (VB) | |
| CV1 | 1.0μF±10%, 25V | Smooths the Vcc power supply | Note 1 |
| CV2 | 33nF±10%, 400V | Smooths the Vs power supply | Note 1 |
| C1, C2 | 0.22μF±10%, 25V | For charge pump | |
| C3, C4, C5 | 1000pF±10%, 25V | Eliminates Hall signal noise | Note 2 |
| Rs | 1Ω±1%, 1W | Sets current limit | Note 3 |
| CTR | 2200pF±5%, 25V | Sets PWM frequency | Note 4 |
| RTR | 11kΩ±5% | | |

Note 1: As necessary, increase the capacitance and add a zener diode in consideration of noise immunity.

Note 2: Optimize the capacitance corresponding to conditions.

Note 3: The current limit set value can be calculated as follows.

$$I = V_{ref1} / R_s \text{ (A)}$$

To determine the shunt resistor Rs, see Table 3.1.1 and Section 4.

Note 4: The PWM frequency is approximated by the following equation.

$$f_{PWM} \approx 0.494 / (CTR \times RTR) \text{ (Hz)}$$

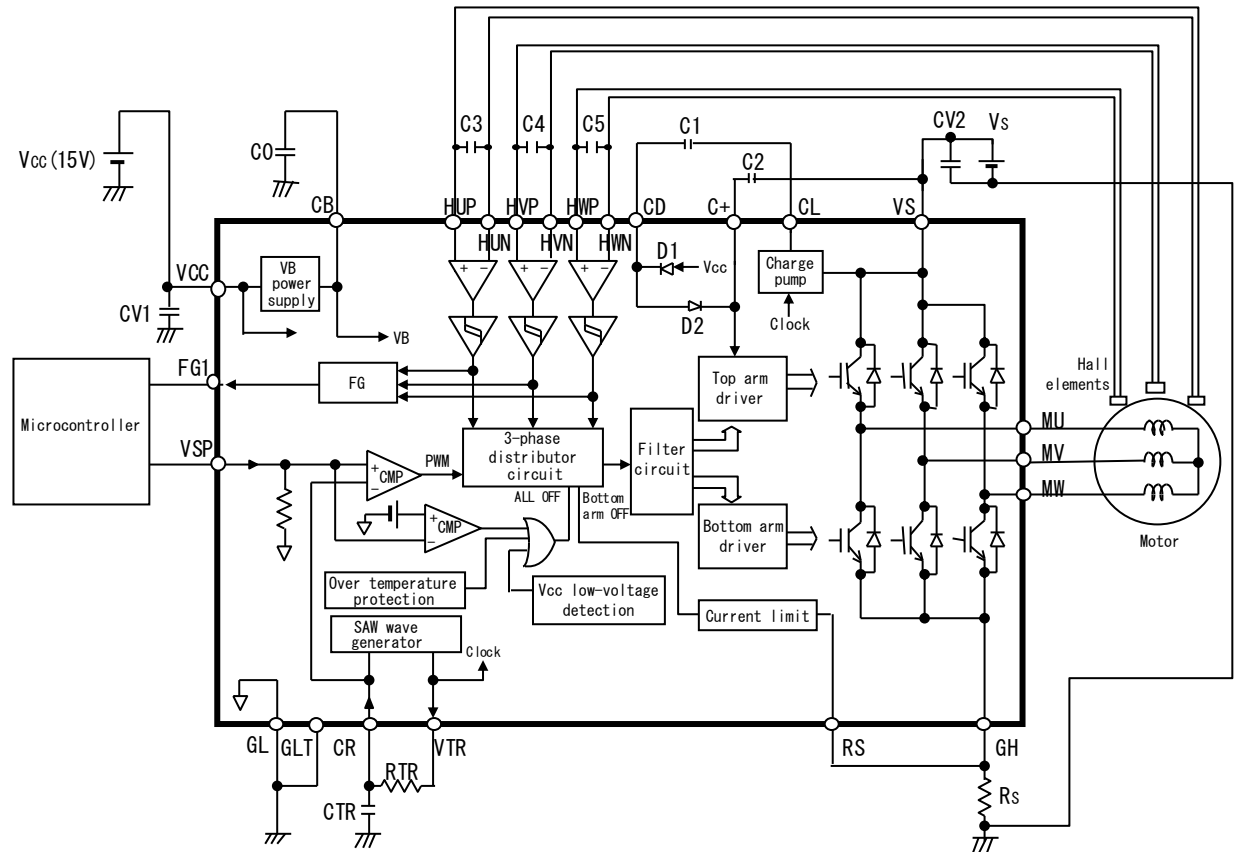


FIGURE 3.1.1 Block Diagram (ECN30114 is shown inside the bold line.)

4. Safe Operation Area (SOA) and Derating

4.1 Safe Operation Area (SOA)

The current and voltage at output pins must not be outside the SOA shown in FIGURE 4.1.1.

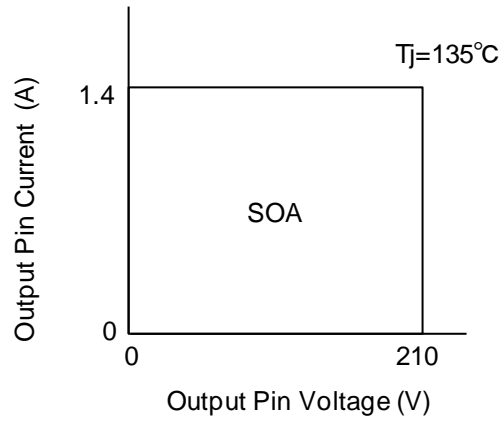


FIGURE 4.1.1 SOA

4.2 General Design Derating Standards

- (a) Temperature - Junction operating temperature must be kept under 110°C .
- (b) Supply voltage - V_s power supply voltage must be kept under 210V.

Junction operating temperature depends on various parameters such as power supply voltages, ambient temperature, load, heat dissipation routes. Test it sufficiently by using actual systems.

5. Pin Locations

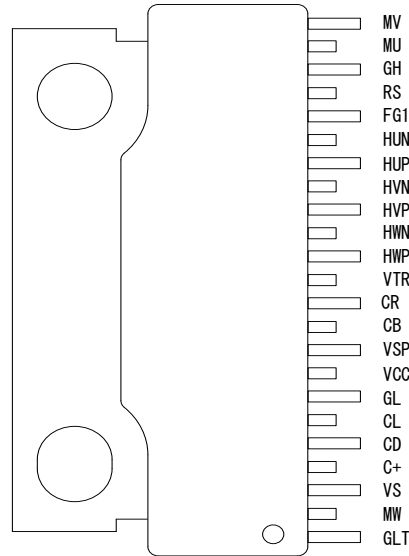


FIGURE 5.1 Pin Locations (Resin surface side)

6. Explanations of Pins

TABLE 6.1 Explanations of Pins

| Pin No. | Symbol | Explanation | Remark |
|---------|--------|--|----------------|
| 1 | GLT | To be set to ground potential | Note 2, Note 3 |
| 2 | MW | W phase output | Note 1 |
| 3 | VS | High voltage power supply | Note 1 |
| 4 | C+ | For the charge pump circuit | Note 1 |
| 5 | CD | For the charge pump circuit | Note 1 |
| 6 | CL | For the charge pump circuit | Note 1 |
| 7 | GL | Ground | Note 2 |
| 8 | VCC | 15V power supply | |
| 9 | VSP | Analog speed command signal input | |
| 10 | CB | VB power supply output | |
| 11 | CR | Connect a resistor and a capacitor to set the PWM frequency | |
| 12 | VTR | Connect a resistor to set the PWM frequency | |
| 13 | HWP | W phase Hall signal plus input | |
| 14 | HWN | W phase Hall signal minus input | |
| 15 | HVP | V phase Hall signal plus input | |
| 16 | HVN | V phase Hall signal minus input | |
| 17 | HUP | U phase Hall signal plus input | |
| 18 | HUN | U phase Hall signal minus input | |
| 19 | FG1 | Output for motor rotational speed monitor | |
| 20 | RS | Current limit input | |
| 21 | GH | Emitters of bottom arm IGBTs and anodes of bottom arm FWDs (Connected to a shunt resistor) | |
| 22 | MU | U phase output | Note 1 |
| 23 | MV | V phase output | Note 1 |

Note 1: High voltage pin. The voltage between CD and CL and the voltage between C+ and VS are low.

Note 2: Connect GLT to GL externally.

Note 3: The potential of tab (IC heat sink) is the same as that of the GLT pin. Set the tab potential to open or the same as that of GL pin.

7. Inspection

Hundred percent inspection shall be conducted on electric characteristics at room temperature. For the operating temperature and recovery temperature of the over temperature protection, equivalent inspections are conducted at room temperature.

8. Precautions for Use

8.1 Attachment

To attach a heat sink to the IC, tightening torque should be 0.39 to 0.78 N·m. Tab should not be soldered.

8.2 Countermeasures against Electrostatic Discharge (ESD)

- (a) Customers need to take precautions to protect ICs from electrostatic discharge (ESD). The material of the container or any other device used to carry ICs should be free from ESD, which can be caused by vibration during transportation. Use of electrically conductive containers is recommended as an effective countermeasure.
- (b) Everything that touches ICs, such as the work platform, machine, measuring equipment, and test equipment, should be grounded.
- (c) Workers should be high-impedance grounded (100kΩ to 1MΩ) while working with ICs, to avoid damaging the ICs by ESD.
- (d) Friction with other materials, such as high polymers, should be avoided.
- (e) When carrying a PCB with a mounted IC, ensure that the electric potential is maintained at a constant level using the short-circuit terminals and that there is no vibration or friction.
- (f) The humidity at an assembly line where ICs are mounted on circuit boards should be kept around 45 to 75 percent using humidifiers or such. If the humidity cannot be controlled effectively, using ionized air blowers (ionizers) is effective.

8.3 High Voltage Pin Insulation

Apply resin coating to the pins that high voltage is impressed to or encapsulate the PCB by resin molding.

8.4 Output Short-circuit Protection

This IC (the product of Hitachi Power Semiconductor Device, hereinafter called "HPSD's IC") could break by a short circuit (ex. load short). Therefore, external protection is needed.

8.5 Maximum Ratings

Regardless of changes in external conditions during use of HPSD's IC, the "maximum ratings" described in this document should never be exceeded when designing electronic circuits that employ HPSD's IC. If maximum ratings are exceeded, HPSD's IC may be damaged or destroyed. In no event shall Hitachi Power Semiconductor Device (hereinafter called "HPSD") be liable for any failure in HPSD's IC or any secondary damage resulting from use at a value exceeding the maximum ratings.

8.6 Derating Design

Continuous high-load operation (high temperatures, high voltages, large currents) should be avoided and derating design should be applied, even within the ranges of the maximum ratings, to ensure reliability.

8.7 Safe Design

The HPSD's IC may fail due to accidents or unexpected surge voltages. Accordingly, adopt safe design features, such as redundancy and measures to prevent misuse, in order to avoid extensive damage in the event of a failure.

8.8 Application

If HPSD's IC is applied to the following uses where high reliability is required, obtain the document of permission from HPSD in advance.

- Automobile, Train, Vessel, etc.

Do not apply HPSD's IC to the following uses where extremely high reliability is required.

- Nuclear power control system, Aerospace instrument, Life-support-related medical equipment, etc.

8.9 Soldering

The peak temperature of flow soldering* must be less than 260°C, and the dip time must be less than 10 seconds. High stress by mounting, such as long time thermal stress by preheating, mechanical stress, etc., can lead to degradation or destruction. Make sure that your mounting method does not cause problem as a system.

* Flow soldering: Only pins enter a solder bath, while the resin or tab does not.

8.10 Others

See "Instructions for Use of Hitachi High-Voltage Monolithic ICs" and "Application Note" for other precautions and instructions on how to deal with these kinds of products.

9. Usage

- (1) HPSD warrants that the HPSD products have the specified performance according to the respective specifications at the time of its sale. Testing and other quality control techniques of the HPSD products by HPSD are utilized to the extent HPSD needs to meet the specifications described in this document. Not every device of the HPSD products is specifically tested on all parameters, except those mandated by relevant laws and/or regulations.
- (2) Following any claim regarding the failure of a product to meet the performance described in this document made within one month of product delivery, all the products in relevant lot(s) shall be re-tested and re-delivered. The HPSD products delivered more than one month before such a claim shall not be counted for such response.
- (3) HPSD assumes no obligation nor makes any promise of compensation for any fault which should be found in a customer's goods incorporating the products in the market. If a product failure occurs for reasons obviously attributable to HPSD and a claim is made within six months of product delivery, HPSD shall offer free replacement or payment of compensation. The maximum compensation shall be the amount paid for the products, and HPSD shall not assume responsibility for any other compensation.
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◆Appendix - Supplementary Data

1. Dimensions

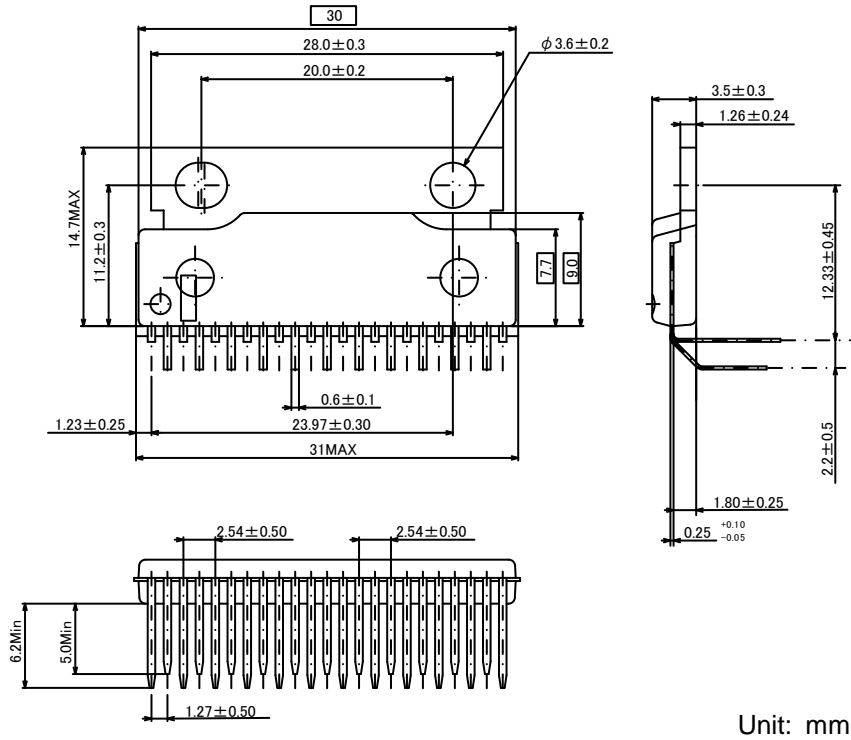


FIGURE A: Dimensions of SP

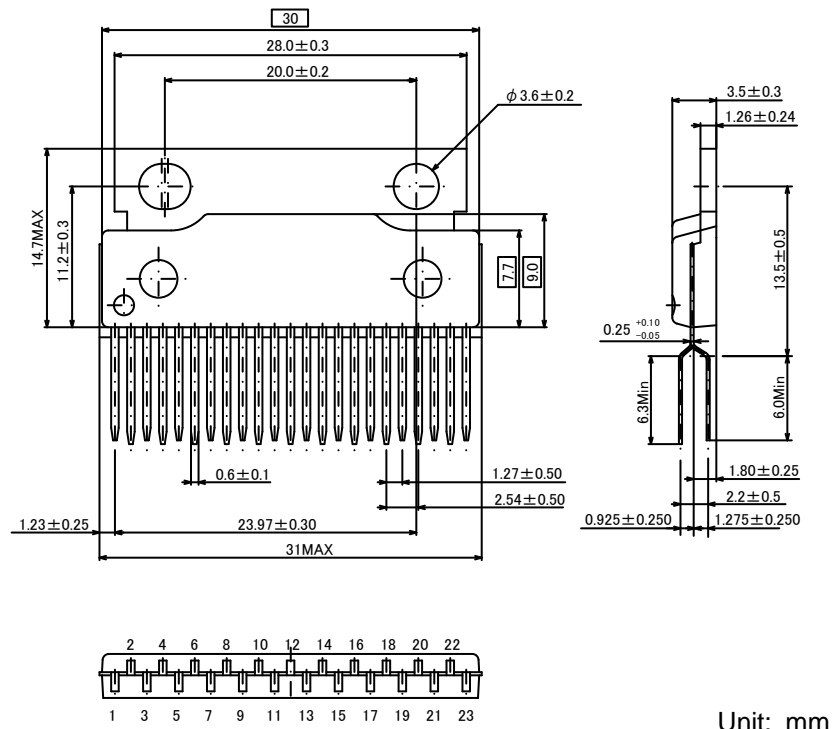
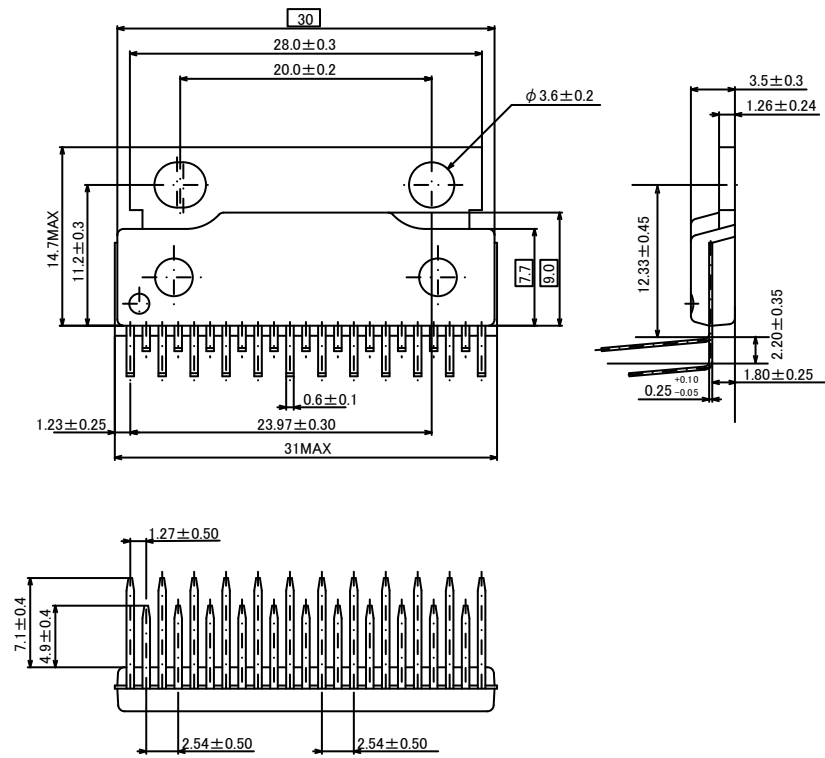


FIGURE B: Dimensions of SPV



Unit: mm

FIGURE C: Dimensions of SPR

2. External Packaging

FIGURE D shows the external packaging.

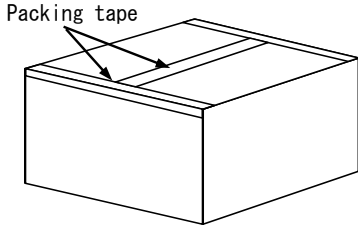
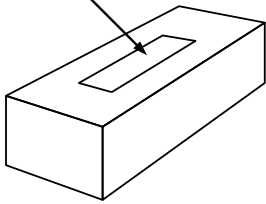
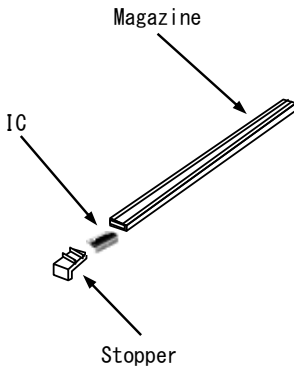
| | Inverter IC |
|-----------|---|
| Outer box |  <p>Packing tape</p> |
| Inner box |  <p>Inner label</p> |
| Magazine |  <p>Magazine</p> <p>IC</p> <p>Stopper</p> <p>The number of ICs: 15 pcs/magazine</p> |

FIGURE D: External Packaging

Precautions for Safe Use and Notices

If semiconductor devices are handled in an inappropriate manner, failures may result. For this reason, be sure to read the latest version of "Instructions for Use of Hitachi High-Voltage Monolithic ICs" before use.



This mark indicates an item requiring caution.



CAUTION

This mark indicates a potentially hazardous situation which, if not avoided, may result in minor or moderate injury and damage to property.



CAUTION

- (1) Regardless of changes in external conditions during use of semiconductor devices, the "maximum ratings" and "safe operating area(SOA)" should never be exceeded when designing electronic circuits that employ semiconductor devices.
- (2) Semiconductor devices may fail due to accidents or unexpected surge voltages. Accordingly, adopt safe design features, such as redundancy and measures to prevent misuse, in order to avoid extensive damage in the event of a failure.
- (3) If semiconductor devices are applied to uses where high reliability is required, obtain the document of permission from HPSD in advance (Automobile, Train, Vessel, etc.). Do not apply semiconductor devices to uses where extremely high reliability is required (Nuclear power control system, Aerospace instrument, Life-support-related medical equipment, etc.).
(If a semiconductor device fails, there may be cases in which the semiconductor device, wiring or wiring pattern will emit smoke or cause a fire or in which the semiconductor device will burst.)

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1. This Data Sheet contains the specifications, characteristics, etc. concerning power semiconductor products (hereinafter called "products").
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